

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination	
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Examiner		Art Unit	Page 1 of 1	
Pierre-Michel Bataille		2186		

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	K	US-			
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	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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